## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Stephen H Tang et al.

FLOATING-BODY DRAM WITH TWO-PHASE WRITE

Docket No.:

80107.038US1

Serial No.: 10/716755

Filed:

November 19, 2003

Due Date: N/A

Examiner:

Unknown

Group Art Unit: 2818

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

We are transmitting herewith the following attached items (as indicated with an "X"):

A return postcard. <u>X</u>

An Information Disclosure Statement (2 pgs.), Form 1449 (1 pg.), and copies of 6 cited documents.

If not provided for in a separate paper filed herewith, Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional fees or credit overpayment to Deposit Account No. 50-2359.

LeMoine Patent Services, PLLC c/o PortfolioIP P.O. Box 52050, Minneapolis, MN 55402 (952-473-8800)

Atty: Dana LeMoine Reg. No. 40,062

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this \_\_\_\_ day of March, 2004.

(GENERAL)

OIPE CS/N 10/716755

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Applicant:

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Title:

FLOATING-BODY DRAM WITH TWO-PHASE WRITE

Assignee:

**Intel Corporation** 

## INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 50-2359 in order to have this Information Disclosure Statement considered.

Serial No. 10/716755

Date Filed: November 19, 2003

Title: FLOATING-BODY DRAM WITH TWO-PHASE WRITE

Dkt. 80107.038US1 Assignee: Intel Corporation

The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

STEPHEN H TANG ET AL.

By their Representatives,

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Date 3-5-04

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on of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO Complete if Known INFORMATION DISCLOSURE 10/716755 **Application Number** November 19, 2003 Filing Date **First Named Inventor** Tang, Stephen 2818 **Group Art Unit** Unknown **Examiner Name** Attorney Docket No: 80107.038US1

US PATENT DOCUMENTS									
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate			

FOREIGN PATENT DOCUMENTS									
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>			

	OTHER	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*			
		FAZAN, PIERRE, et al., "A Simple 1-Transistor Capacitor-Less Memory Cell for High Performance Embedded DRAMs", <u>IEEE 2002 Custom Integrated Circuits Conference</u> , (2002),99-102	
		OHSAWA, TAKASHI, et al., "A Memory Using One-Transistor Gain Cell on SOI(FBC) with Performance Suitable for Embedded DRAM's", 2003 Symposium on VLSI Circuits Digest of Technical Papers, (2003),4 pages	
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		OHSAWA, TAKASHI, et al., "Memory Design Using One-Transistor Gain Cell on SOI", <u>ISSCC 2002</u> , <u>Session 9</u> , <u>Dram and Ferroelectric Memories</u> , <u>9.1</u> , (February 5, 2002), 3 pages	
		OKHONIN, S., "A Capacitor-Less 1T-DRAM Cell", <u>IEEE Electron Device Letters</u> , vol. 23, no. 2, (February 2002),85-87	
		OKHONIN, S., et al., "A SOI Capacitor-less 1T-DRAM Concept", 2001 IEEE International SOI Conference, (October 2001),153-154	

**EXAMINER** 

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